



# PSMN1R5-30YLC

N-channel 30 V 1.55mΩ logic level MOSFET in LPAK using NextPower technology

3 June 2021

Product data sheet

## 1. General description

Logic level enhancement mode N-channel MOSFET in LPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads
- Ultra low R<sub>ds(on)</sub> and low parasitic inductance

## 3. Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

## 4. Quick reference data

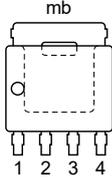
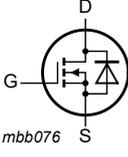
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>	[1]	-	200	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>	-	-	179	W
T <sub>j</sub>	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>	-	1.65	2.05	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>	-	1.3	1.55	mΩ
<b>Dynamic characteristics</b>						
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	8.6	-	nC
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	65	-	nC

[1] 200A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK56; Power-SO8 (SOT669)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R5-30YLC	LPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R5-30YLC	1C530L

## 8. Limiting values

Table 5. Limiting values

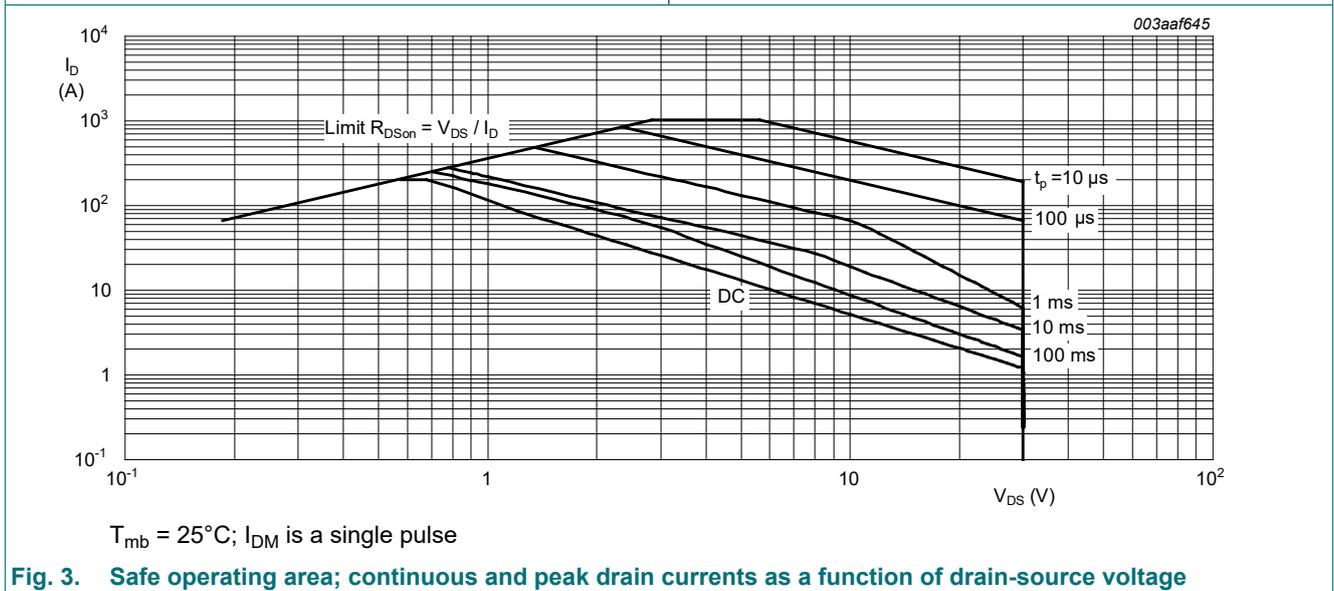
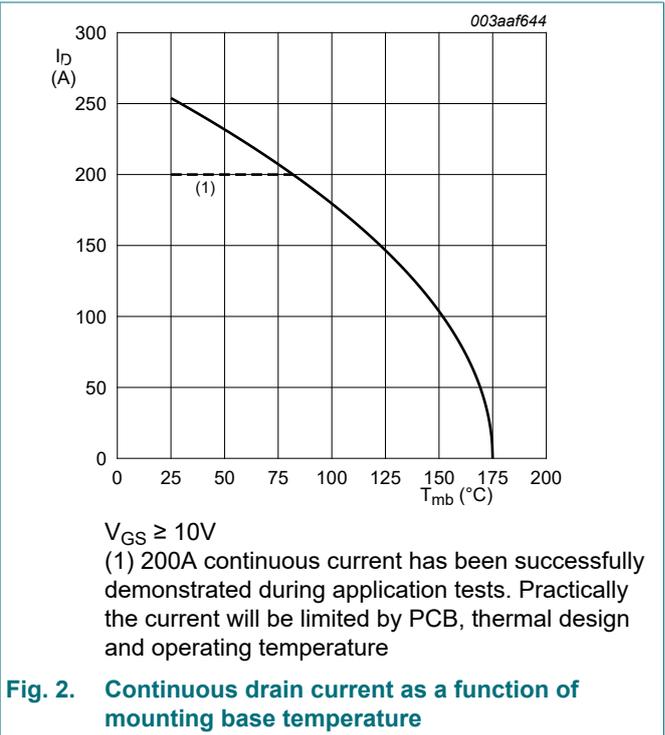
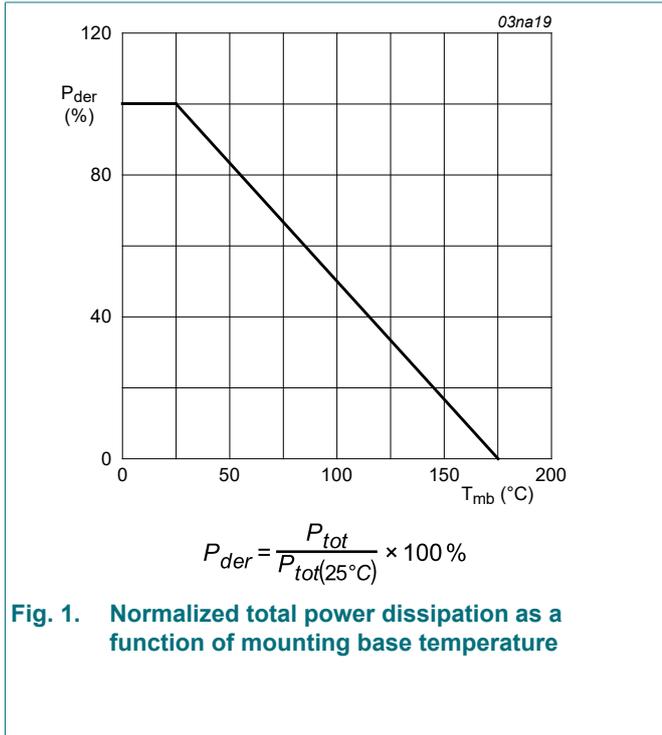
In accordance with the Absolute Maximum Rating System (IEC 60134).

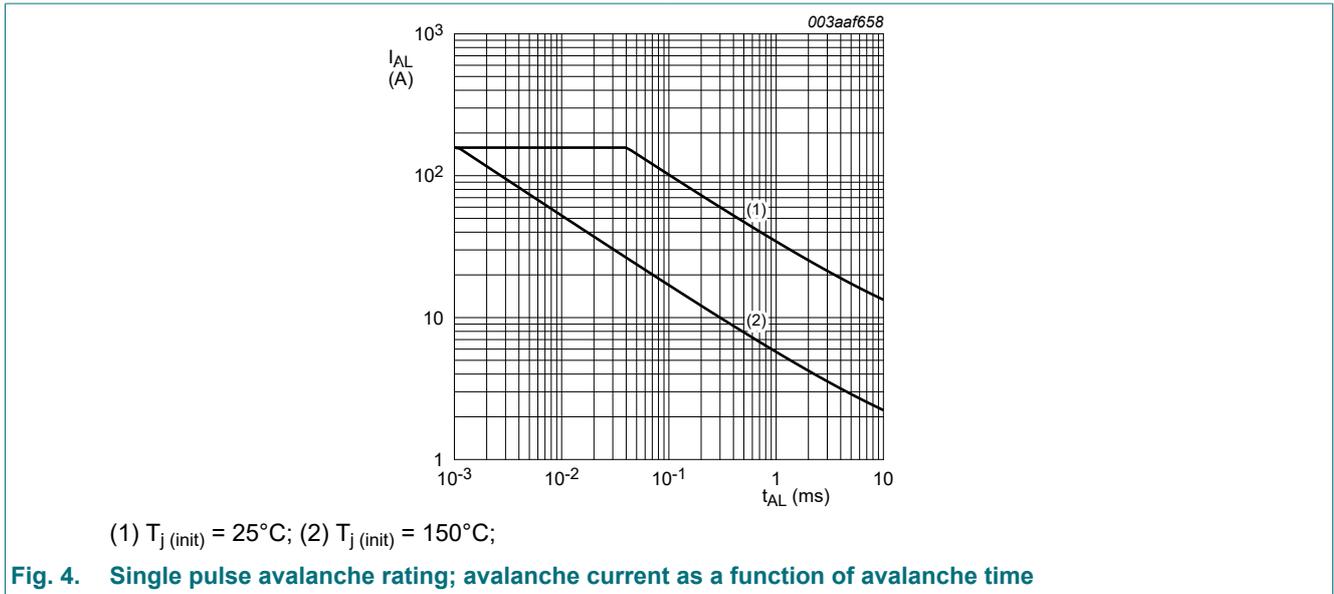
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; Fig. 1	-	179	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2	[1]	200	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2		179	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3	-	1016	A
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
$V_{ESD}$	electrostatic discharge voltage	machine model according to JEDEC JESD22-A115	1000	-	V
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	163	A

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Symbol	Parameter	Conditions	Min	Max	Unit
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \mu s$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	1016	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100 \text{ A}$ ; $V_{sup} \leq 30 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; unclamped	-	147	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 30 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $R_{GS} = 50 \Omega$ ; <a href="#">Fig. 4</a>	[2]	158	A

- [1] 200A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test.

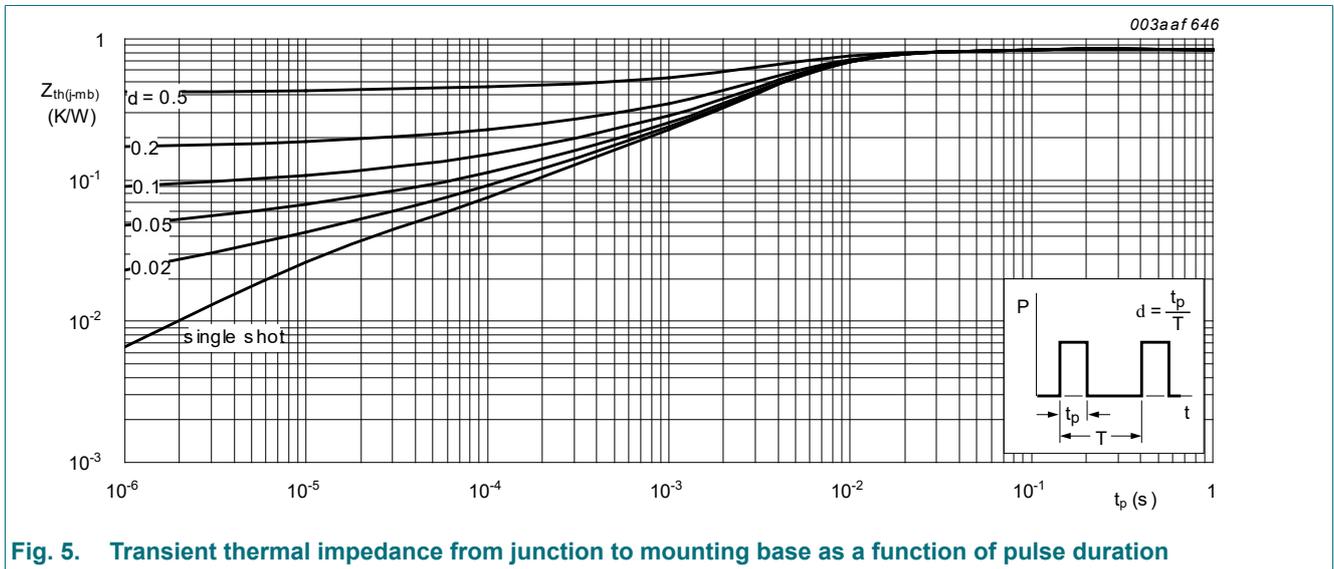




### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.71	0.84	K/W



### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}; T_j = 25^\circ\text{C}$	30	-	-	V
		$I_D = 250\ \mu\text{A}; V_{GS} = 0\ \text{V}; T_j = -55^\circ\text{C}$	27	-	-	V

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>	1.05	1.51	1.95	V
		I <sub>D</sub> = 10 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 150 °C	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>	-	1.65	2.05	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	-	3.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>	-	1.3	1.55	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	-	2.6	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.05	2.1	Ω
<b>Dynamic characteristics</b>						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	65	-	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	30	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	53	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	9.7	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	6.6	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	8.6	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	2.53	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>	-	4044	-	pF
C <sub>oss</sub>	output capacitance		-	860	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	287	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; R <sub>L</sub> = 0.6 Ω; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 4.7 Ω	-	33	-	ns
t <sub>r</sub>	rise time		-	62	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	62	-	ns
t <sub>f</sub>	fall time		-	38	-	ns
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	23	-	nC
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V	-	41	-	ns
Q <sub>r</sub>	recovered charge		-	43	-	nC

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_a$	reverse recovery rise time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 15 \text{ V}$ ; <a href="#">Fig. 18</a>	-	24	-	ns
$t_b$	reverse recovery fall time		-	17	-	ns

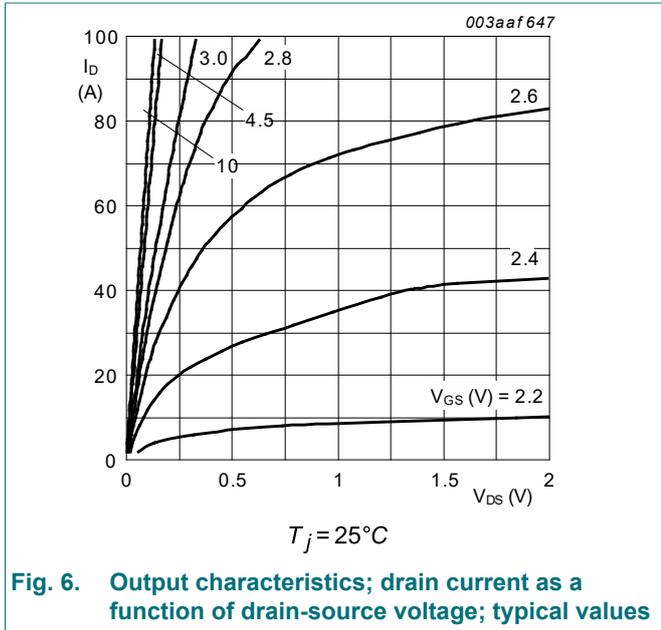


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

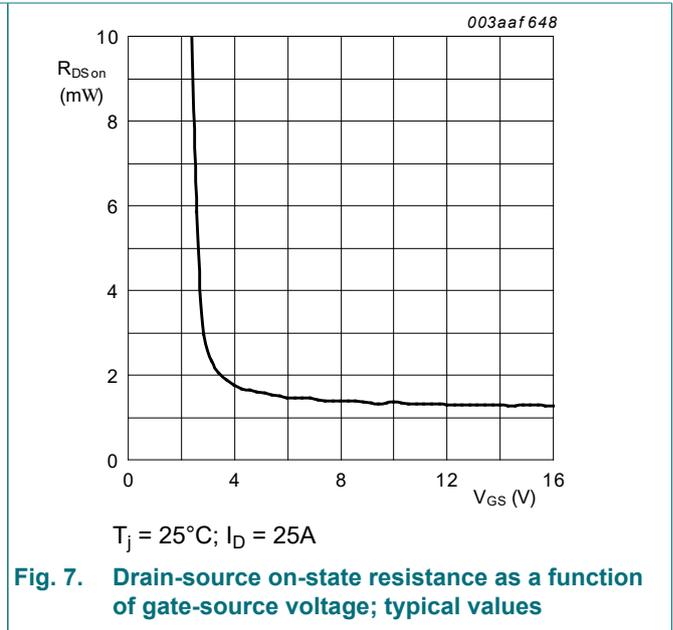


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

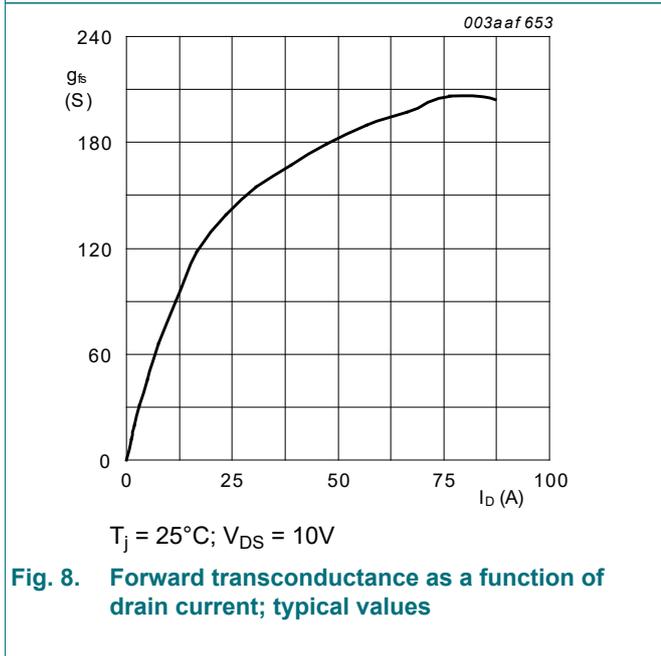


Fig. 8. Forward transconductance as a function of drain current; typical values

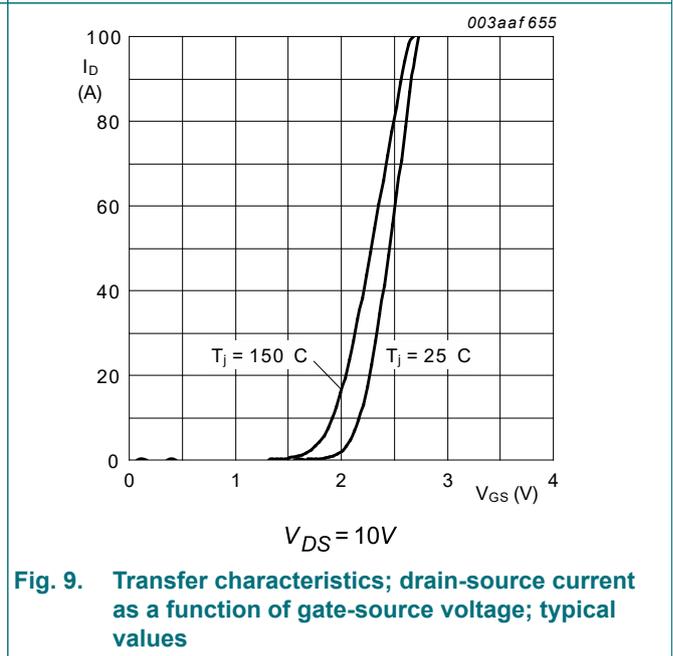


Fig. 9. Transfer characteristics; drain-source current as a function of gate-source voltage; typical values

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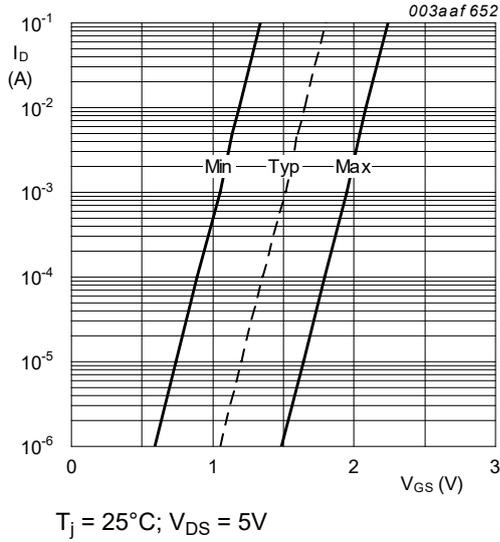


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

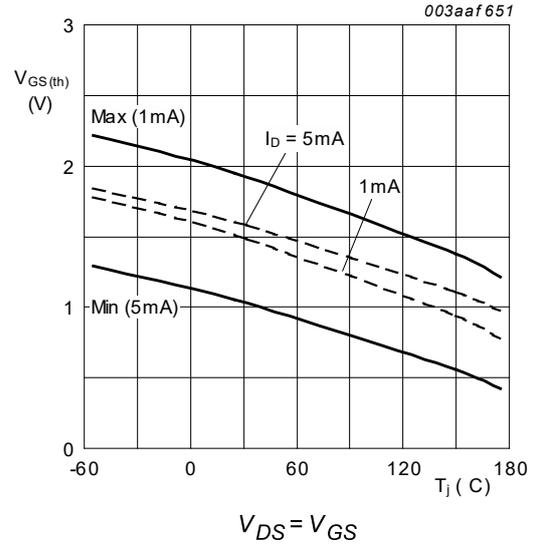


Fig. 11. Gate-source threshold voltage as a function of junction temperature

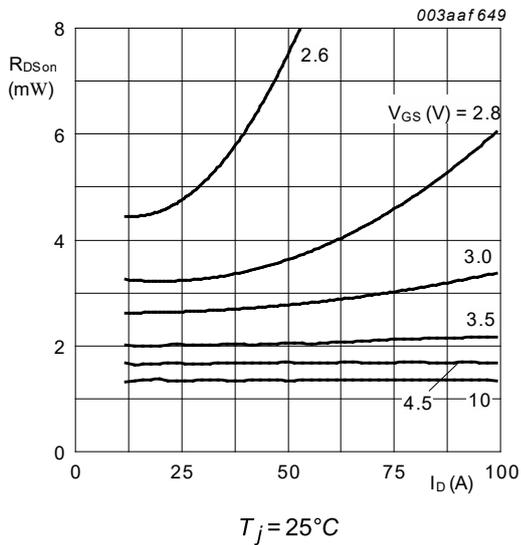


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

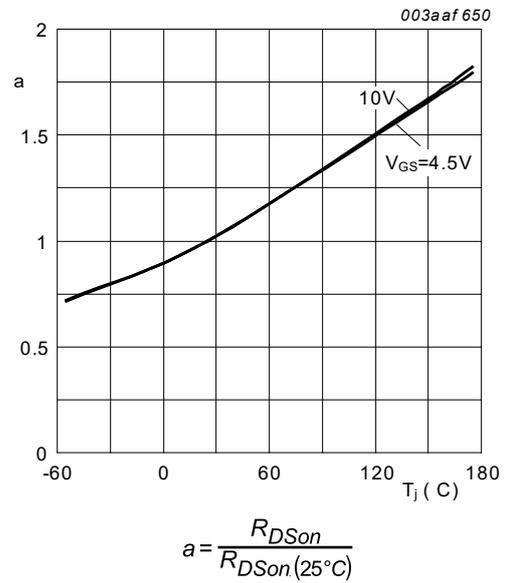


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

N-channel 30 V 1.55mΩ logic level MOSFET in LPAK using NextPower technology

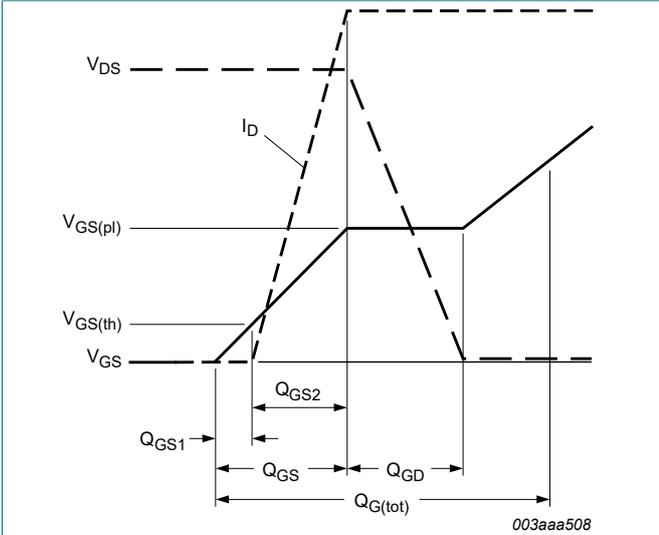


Fig. 14. Gate charge waveform definitions

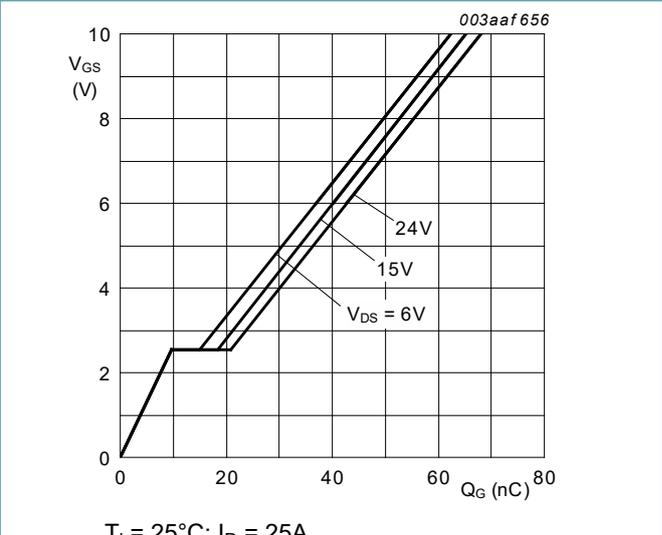


Fig. 15. Gate-source voltage as a function of gate charge; typical values

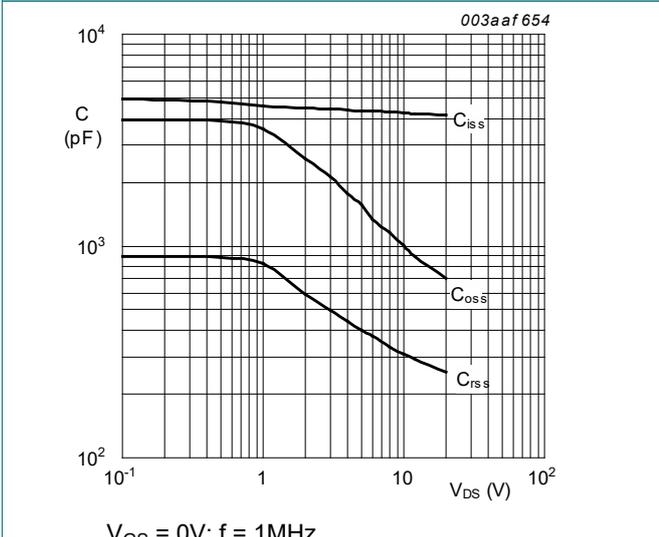


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

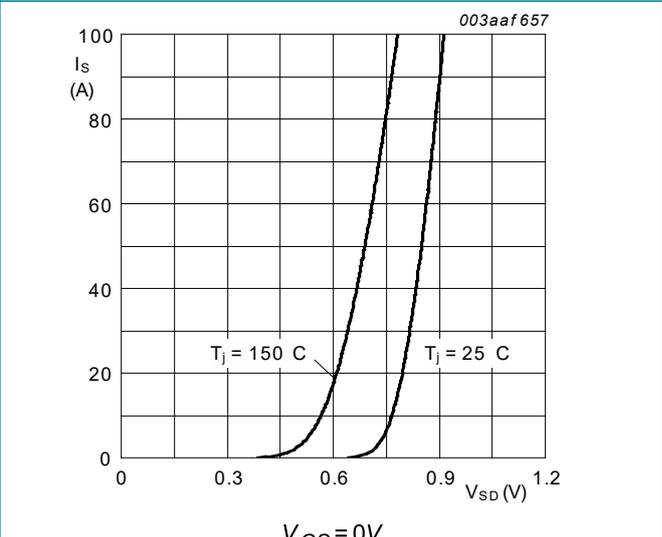


Fig. 17. Source current as a function of source-drain voltage; typical values

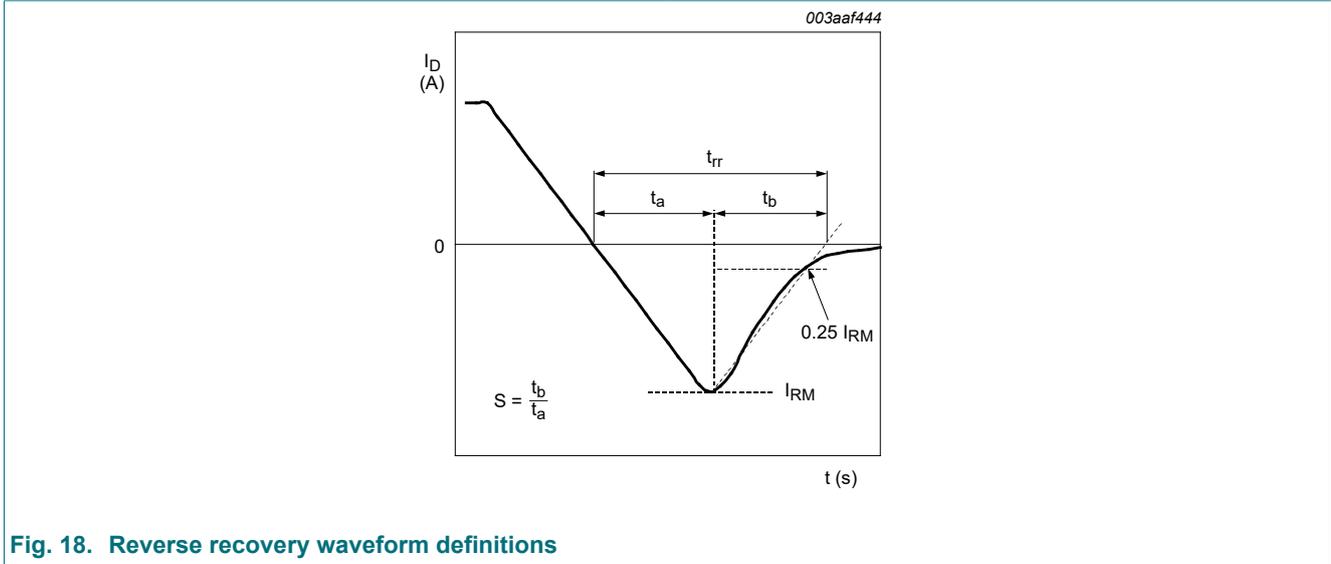


Fig. 18. Reverse recovery waveform definitions

### 11. Package outline

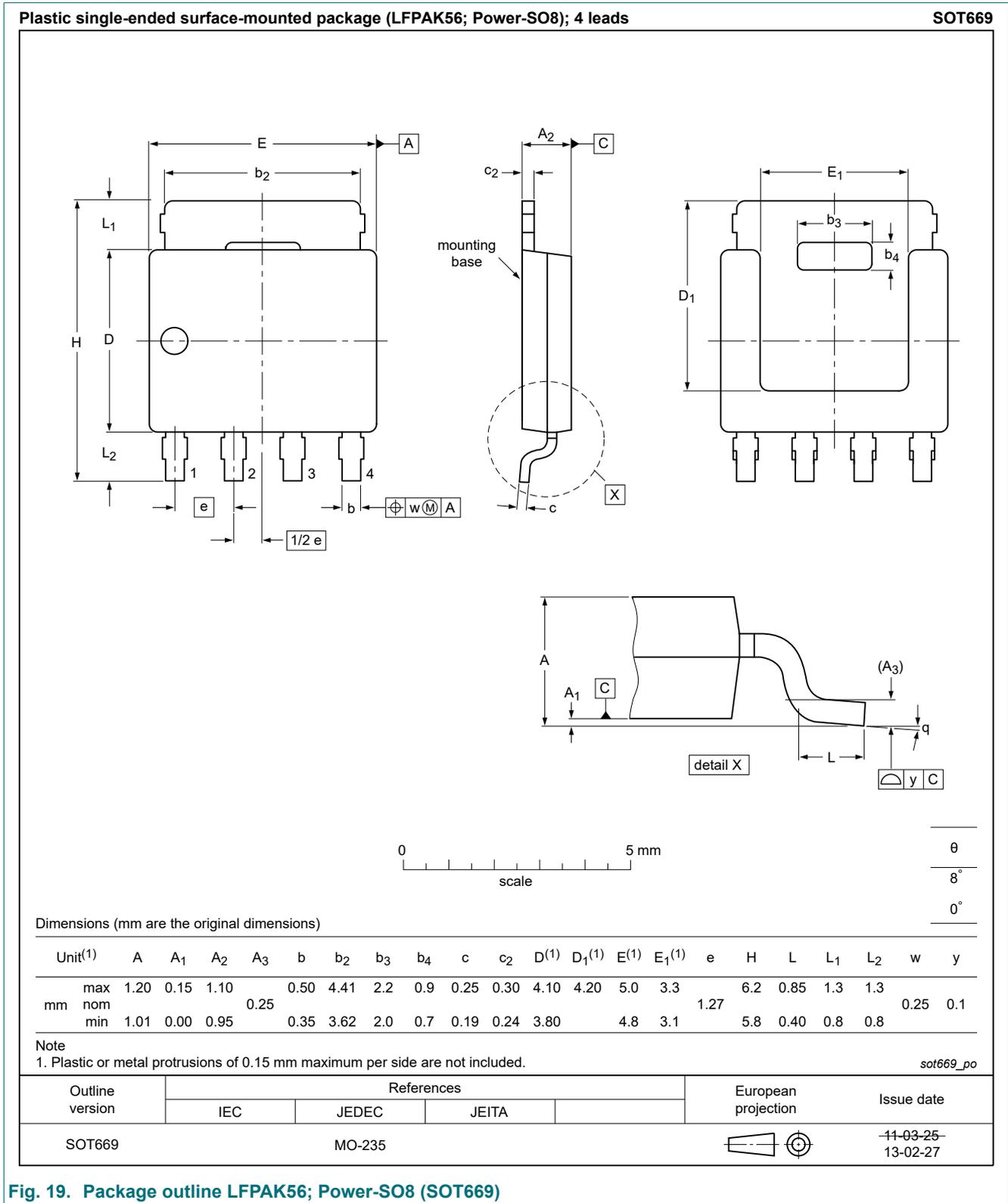


Fig. 19. Package outline LPAK56; Power-SO8 (SOT669)

## 12. Soldering

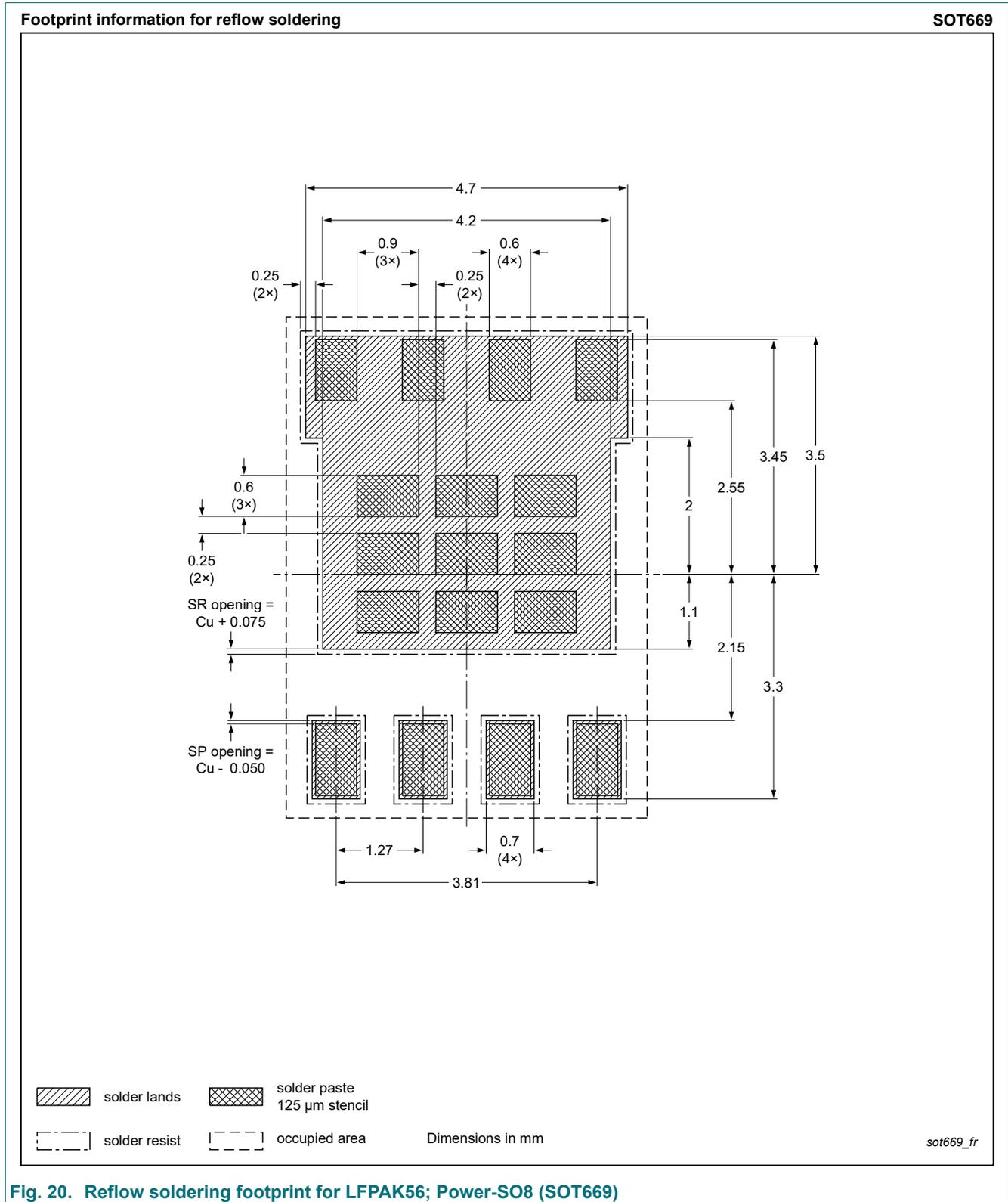
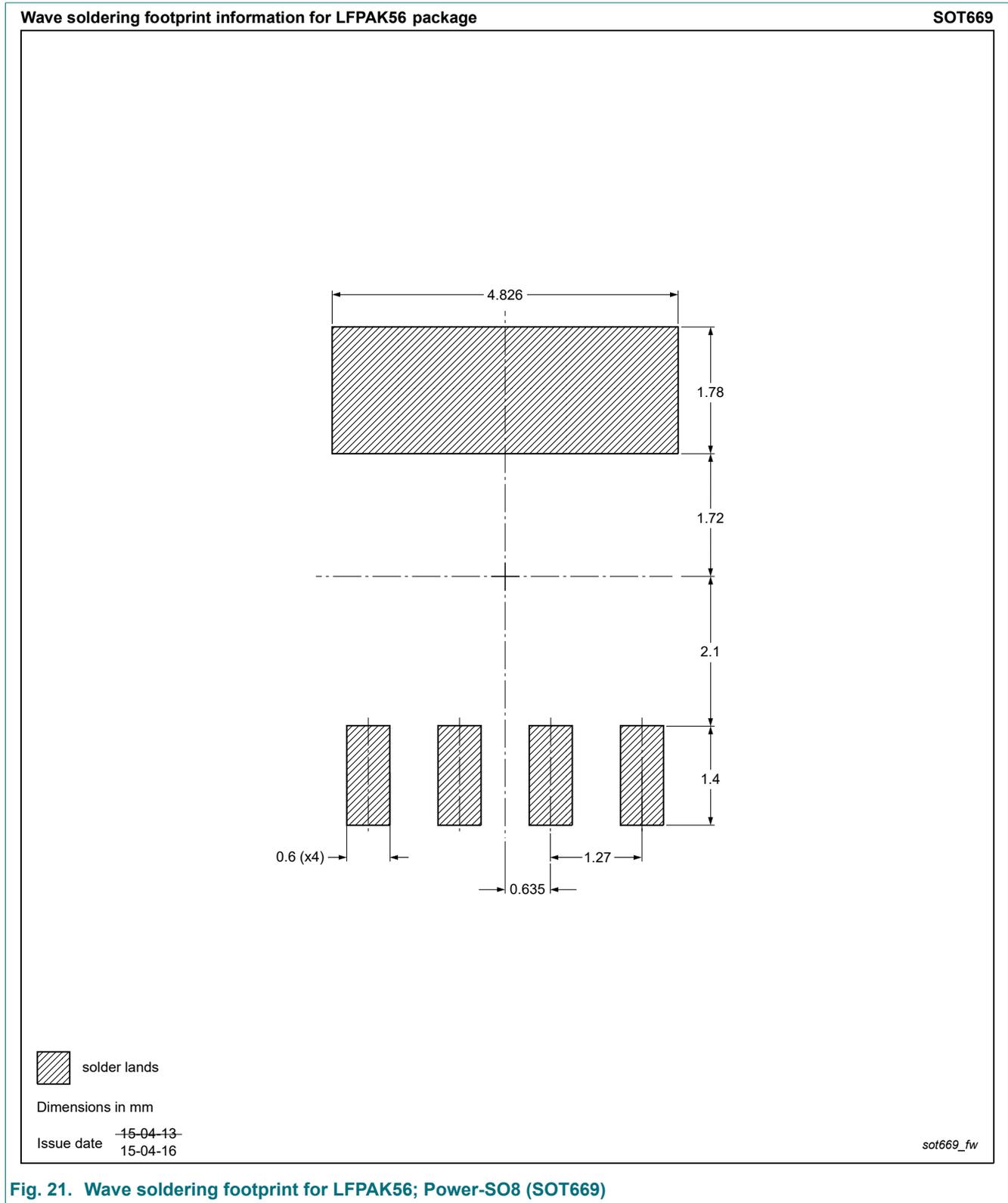


Fig. 20. Reflow soldering footprint for LPAK56; Power-SO8 (SOT669)



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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